

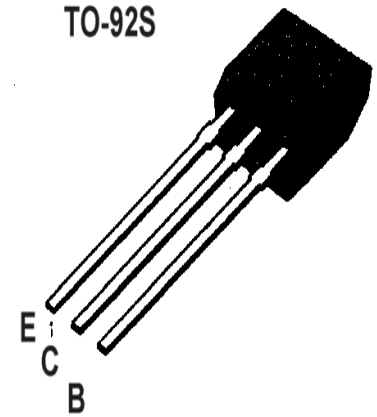
NPN Transistors

—NPN Silicon—

■■ **APPLICATION:** Audio Frequency Low Power Amplifier Applicatio

■■ **MAXIMUM RATINGS** (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	35	V
Collector-emitter voltage	V _{CEO}	30	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	0.5	A
Collector Power Dissipation	P _C	0.3	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



■■ **ELECTRICAL CHARACTERISTICS** (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION		
Collector-Base Breakdown Voltage	BV _{CBO}	35			V	I _C =20uA	I _E =0	
Collector-Emitter Breakdown Voltage	BV _{CEO}	30			V	I _C =1mA	I _B =0	
Emitter-Base Breakdown Voltage	BV _{EBO}	5			V	I _E =20uA	I _C =0	
Collector Cut-off Current	I _{CBO}			0.1	uA	V _{CB} =35V	I _E =0	
Emitter Cut-off Current	I _{EBO}			0.1	uA	V _{EB} =5V	I _C =0	
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.25	V	I _C =0.1A	I _B =10mA	
DC Current Gain	H _{FE}	70		400	β	V _{CE} =6V	I _C =2mA	
Gain bandwidth product	f _T	80			MHz	V _{CE} =1V	I _C =0.1A	
Common Base Output Capacitance	Cob		2	3.5	pF	V _{CB} =10V	I _E =0	f=1MHz
Noise Figure	NF			7	dB	Vce=6V	Ic=1mA	f=1KHz

■■ **h_{FE}(I) Classification And Marking**

Print Mark	C1959
Classification	
hFE	70-400